

(11)Publication number:

10-112460

(43) Date of publication of application: 28.04.1998

(51)Int.CI.

H01L 21/316

(21)Application number : 09-165471

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(22)Date of filing:

23.06.1997

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(30)Priority

Priority number: 08211796

Priority date: 12.08.1996

Priority country: JP

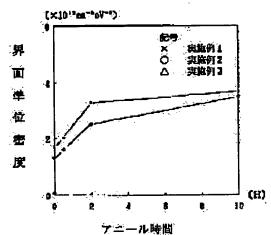
(54) MANUFACTURE OF SILICON CARBIDE SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce the interface level density after formation of a thermal oxide film of a silicon carbide semiconductor device.

SOLUTION: The anneal time in inert gas after thermal oxidation is made under two hours. Moreover, it will do to heat-treat the thermal oxide film made once in gas including hydrogen atoms such as hydrogen, water, or the like at a low temperature of 300-500°C.

Furthermore, after thermal oxidation and in one part at least of the cooling period after heat-treatment process and thermal oxidation, the gas including hydrogen atoms i5 made atmosphere.



LEGAL STATUS

[Date of request for examination]

08.08.2002

[Date of sending the examiner's decision of

rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

3525149

[Date of registration]

27.02.2004

[Number of appeal against examiner's decision

of rejection]

[Date of requesting appear ainst examiner's decision of rejection] [Date of extinction of right]

